

## TEOS Silicon Oxide

This process will deposit PECVD oxide using TEOS.

Material	SiO <sub>2</sub>
Substrate Size	Die to 8" (200mm)
Deposition Rate	>500 Å /min
Uniformity	<5 %
Refractive Index	1.45-1.5 ±0.05
Step Coverage	Conformal
Stress	Compressive
Reproducibility	<± 2.5%

Additional stress control can be achieved by adding the Triode option.

For more information, contact:

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